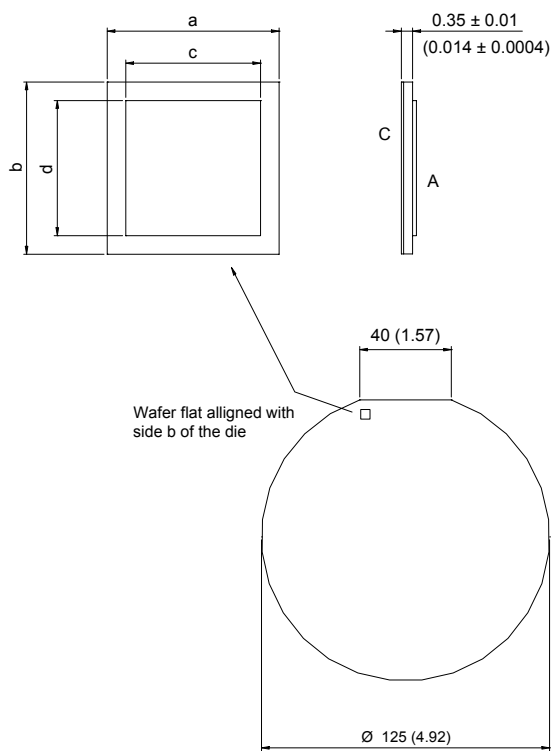


International
IOR Rectifier

FD120H06A5B

Fred Die in Wafer Form



NOTES:

1. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).

2. CONTROLLING DIMENSION (INCH):

3. DIMENSIONS AND TOLERANCES:

a = 3.048 ± 0.05
 (0.120 ± 0.002)
b = 3.048 ± 0.05
 (0.120 ± 0.002)
c = 2.388 ± 0.003
 (0.094 ± 0.0001)
d = 2.388 ± 0.003
 (0.094 ± 0.0001)

4. LETTER DESIGNATION:

A = Anode (Top Metal)
 C = Cathode (Back Metal)

5. SAWING:

Recommended Blade
 SEMITEC S1025 QS00 Blade

6. MINIMUM ORDER QUANTITY:

900 die

NOT TO SCALE

Reference IR Packaged Part: 15ETH06 Series

FD120H06A5B

Preliminary Data Sheet PD-20183 rev. A 06/01



Electrical Characteristics (Wafer Form)

Parameters	Units	Test Conditions
V _{FM} Maximum Forward Voltage	2.3V	T _J = 25°C, I _F = 15 A
V _{RRM} Mimunum Reverse Breakdown Voltage	600V	T _J = 25°C, I _{RRM} = 200 μA
I _{RM} Max. Reverse Leakage Current	100μA	T _J = 25°C, V _{RRM} = 600 V
t _{tr} Typ. Reverse Recovery Time	20 ns	I _F = 1A, di/ dt = 100A/μs, V _R = 30 V

Mechanical Data

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 2 KA - 3 KA)
Nominal Front Metal Composition, Thickness	99% Al, 1% Si (3 microns)
Chip Dimensions	0.120" x 0.120" (see drawing)
Reject Ink Dot Size	0.25mm diameter minimum
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

Ordering Information Table

Device Code

FD	120	H	06	A	5	B
①	②	③	④	⑤	⑥	⑦

- 1** - Fred Die
- 2** - Chip Dimension in Mils: 120 = 120x120 square
- 3** - Process H = HyperFast
- 4** - Voltage code Vrrm (*100) eg: 06 = 600V
- 5** - Chip surface metallization: A = Aluminium (anode), Silver (cathode)
- 6** - Wafer diameter in inches
- 7** - Packaging: B = Inked Probed Unsawn Wafer (Wafer in box)